

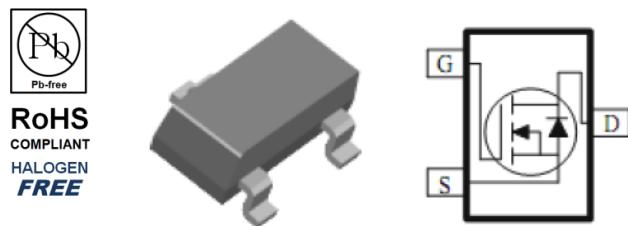
Key Features:

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (mΩ)	I_D (A)
-20	79 @ $V_{GS} = -4.5V$	-3.4
	110 @ $V_{GS} = -2.5V$	-2.9

Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current ^a	$T_A=25^\circ C$	I_D	-3.4	A
	$T_A=70^\circ C$		-2.6	
Pulsed Drain Current ^b		I_{DM}	-10	
Continuous Source Current (Diode Conduction) ^a		I_S	-1.9	
Power Dissipation ^a	$T_A=25^\circ C$	P_D	1.3	W
	$T_A=70^\circ C$		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 10 \text{ sec}$	$R_{\theta JA}$	100	°C/W
	Steady State		166	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature



Electrical Characteristics

AM2321P

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	-0.4			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16 V$, $V_{GS} = 0 V$			-1	uA
		$V_{DS} = -16 V$, $V_{GS} = 0 V$, $T_J = 55^\circ C$			-25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5 V$, $V_{GS} = -4.5 V$	-5			A
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5 V$, $I_D = -3.2 A$			79	mΩ
		$V_{GS} = -2.5 V$, $I_D = -2.6 A$			110	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15 V$, $I_D = -3.2 A$		5		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1 A$, $V_{GS} = 0 V$		-0.8		V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = -10 V$, $V_{GS} = -4.5 V$, $I_D = -3.2 A$		10		nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			3.1		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = -10 V$, $R_L = 3.2 \Omega$, $I_D = -3.2 A$, $V_{GEN} = -4.5 V$, $R_{GEN} = 6 \Omega$		10		ns
Rise Time	t_r			16		
Turn-Off Delay Time	$t_{d(off)}$			42		
Fall Time	t_f			21		
Input Capacitance	C_{iss}	$V_{DS} = -15 V$, $V_{GS} = 0 V$, $f = 1 \text{ Mhz}$		666		pF
Output Capacitance	C_{oss}			87		
Reverse Transfer Capacitance	C_{rss}			80		

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.